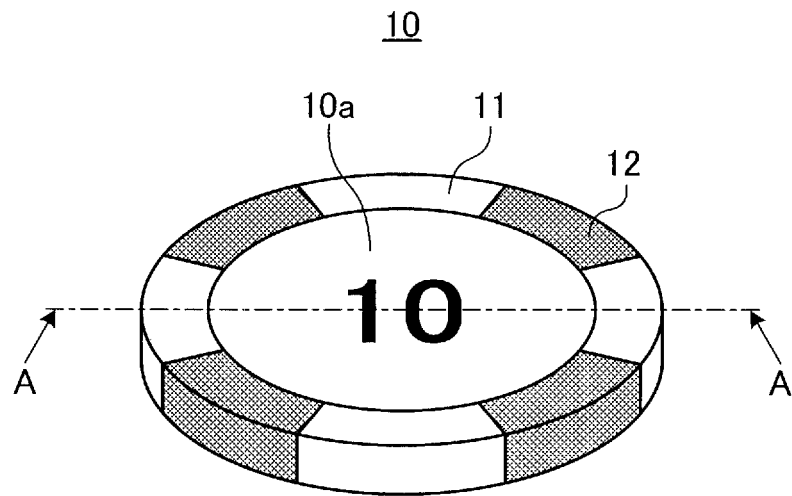
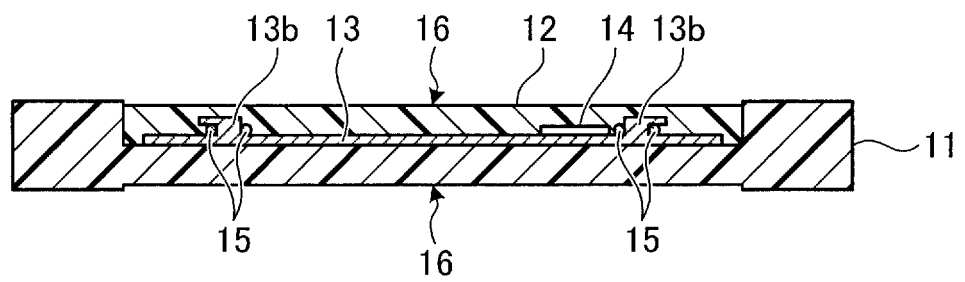


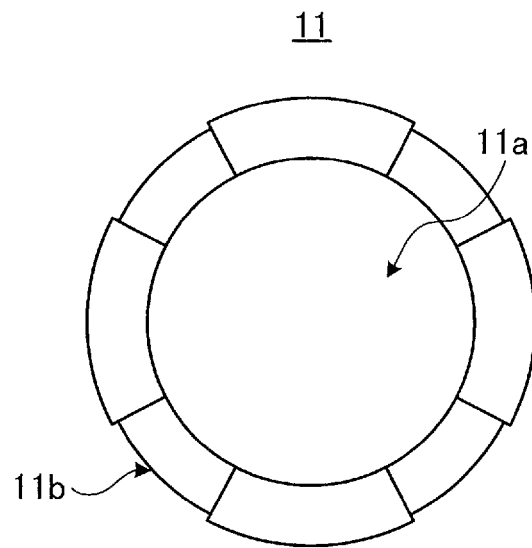
[図1]



[図2]

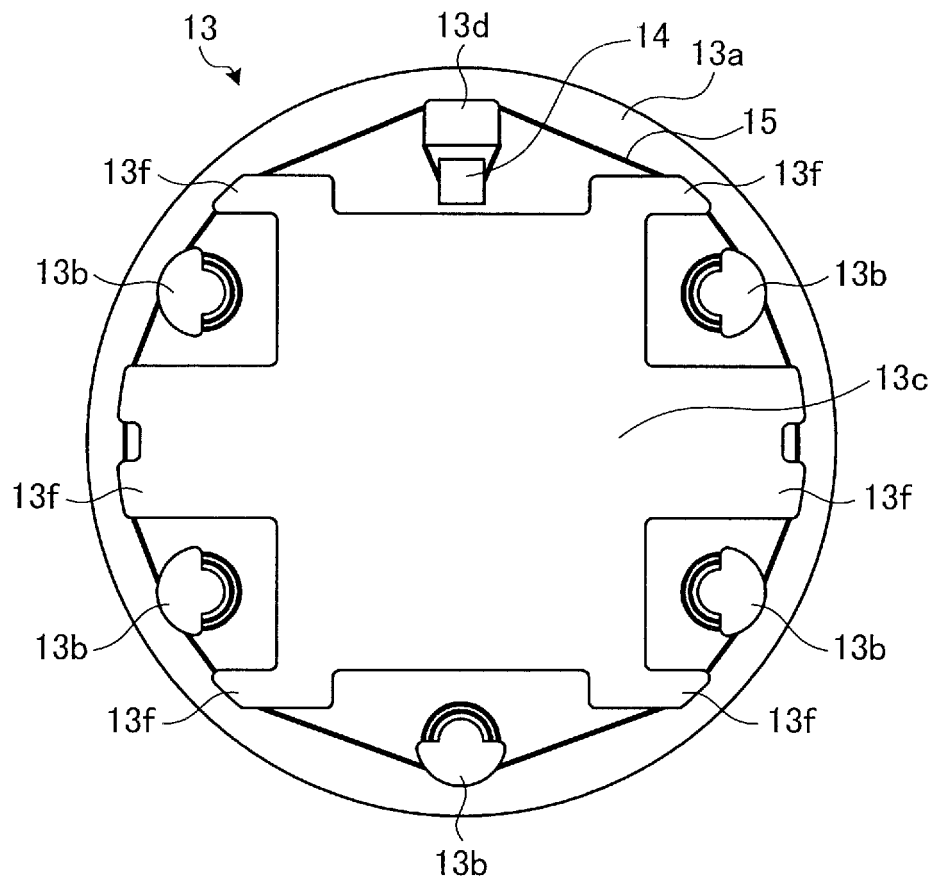


[図3]

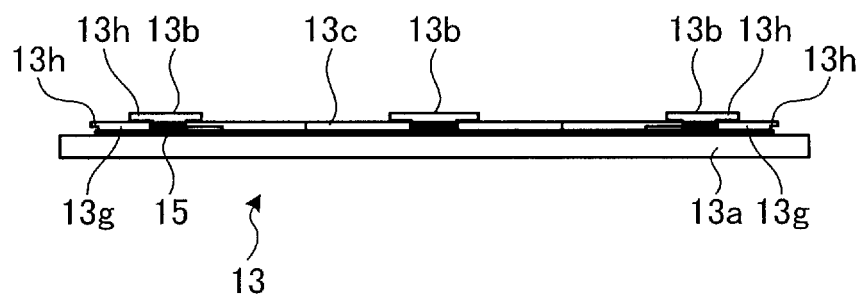


A cross-sectional view of a semiconductor device 13. The device consists of a substrate 13a with a hatched pattern. On the substrate, there are two main regions. The left region includes a layer 13g, a layer 13b, and a top layer 13h. The right region includes a layer 13g, a layer 13b, and a top layer 13h. A central layer 13c is positioned between the two main regions, with an arrow 13d pointing to it. The entire structure is labeled 13.

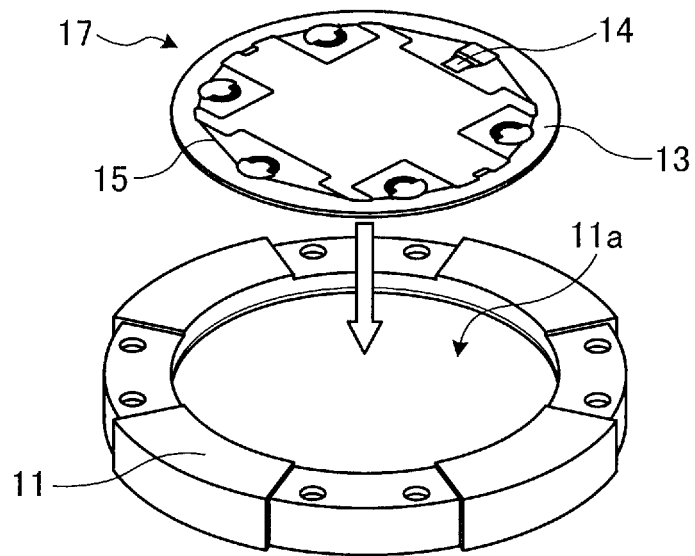
[図5A]



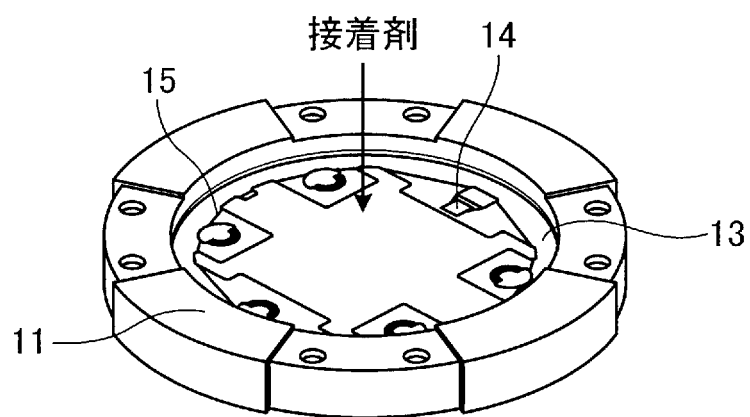
[図5B]



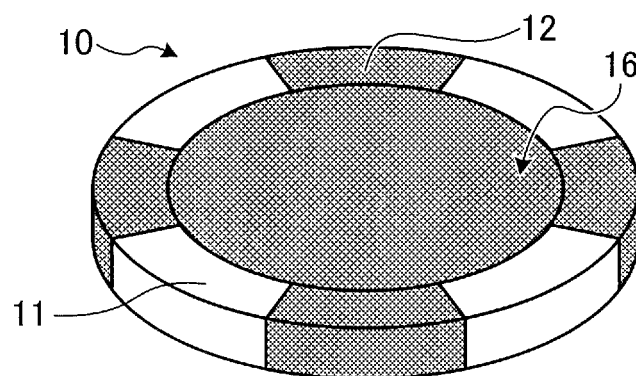
[図6A]



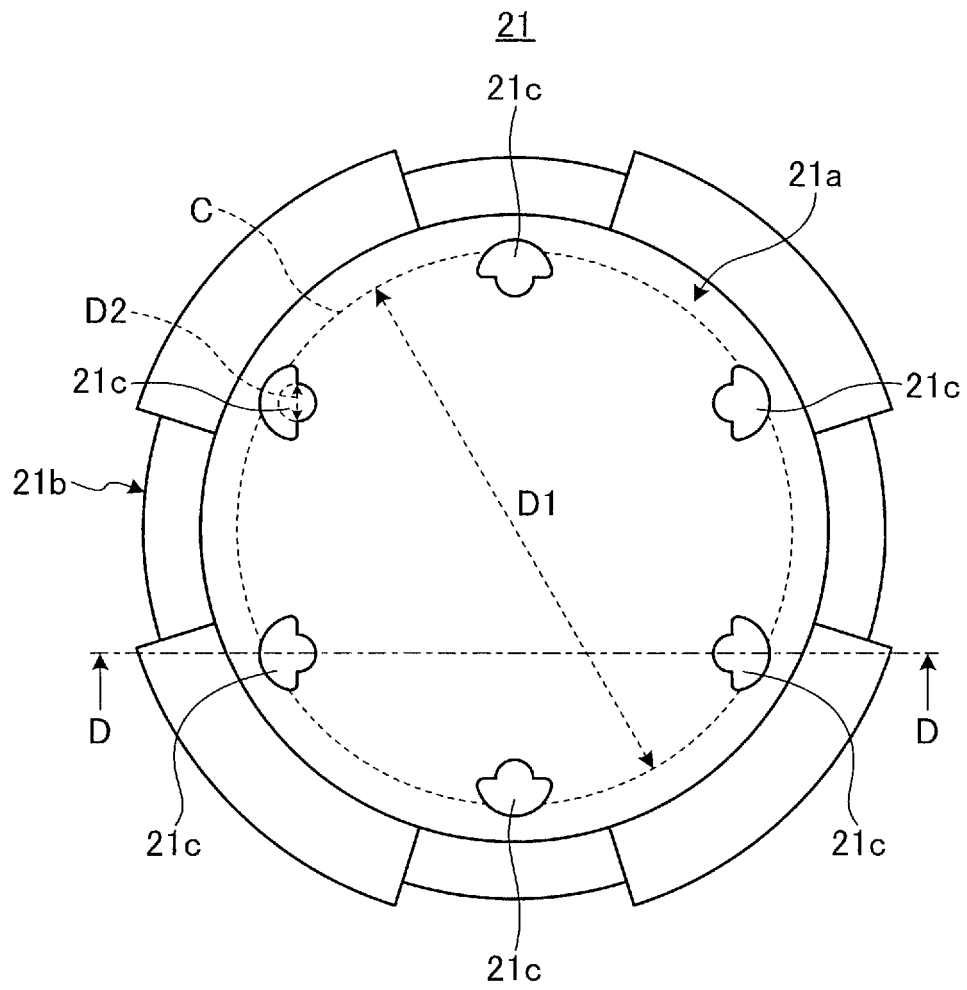
[図6B]



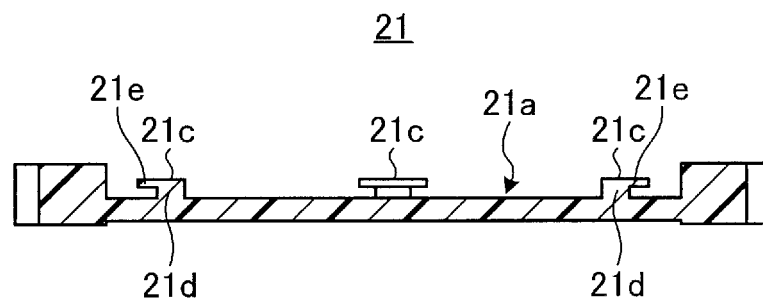
[図6C]



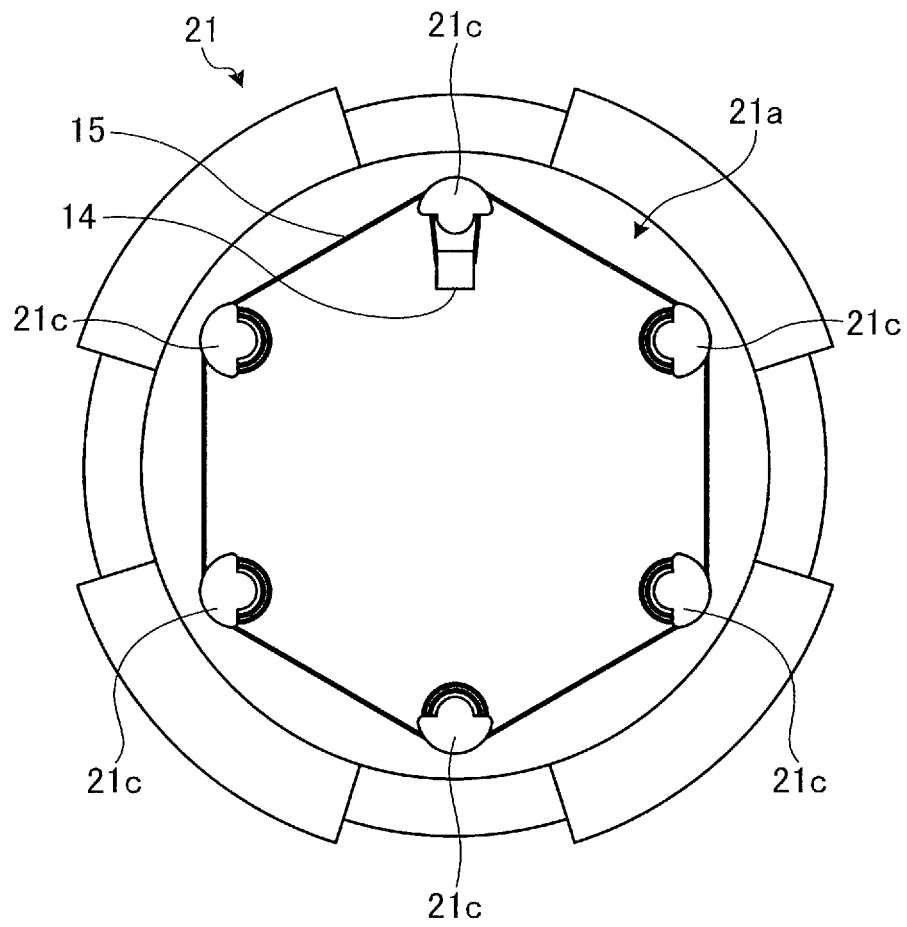
[図7A]



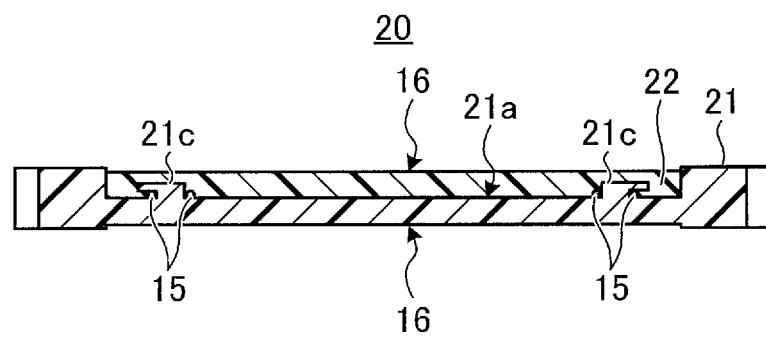
[図7B]



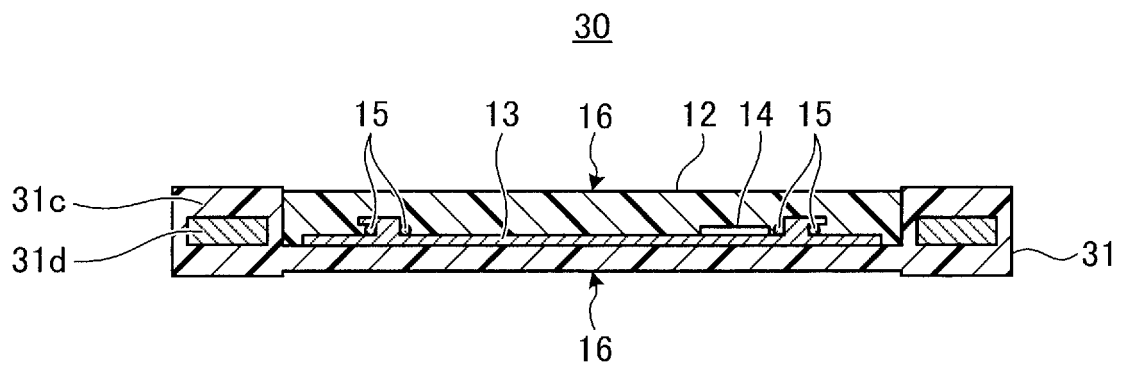
[図8]



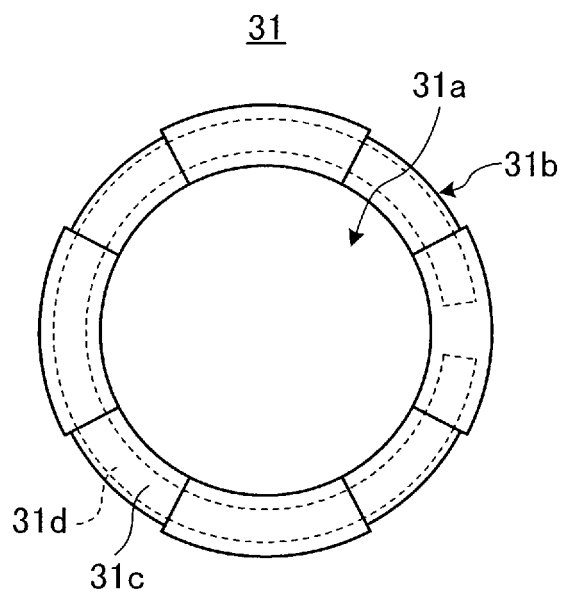
[図9]



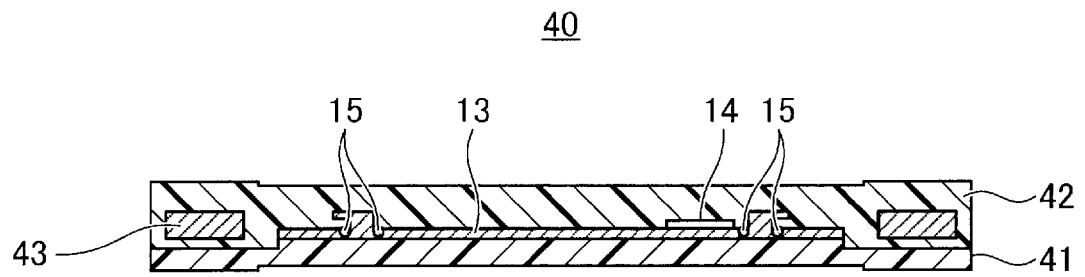
[図10]



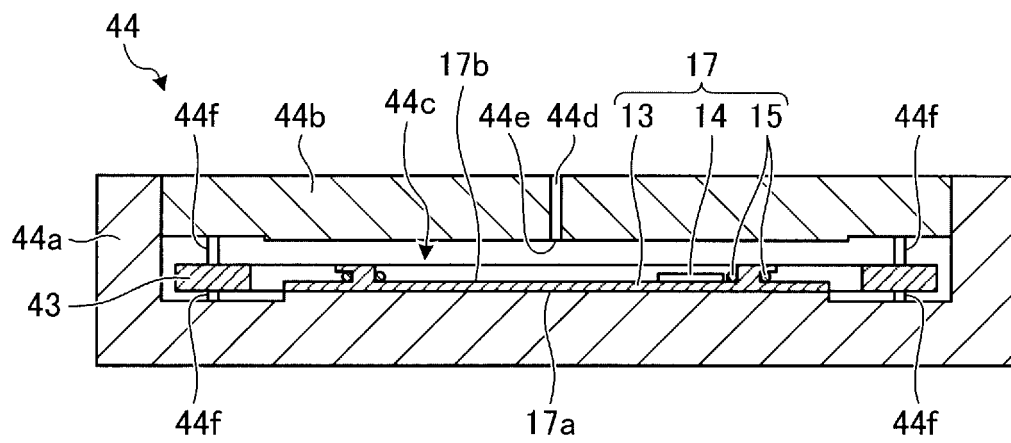
[図11]



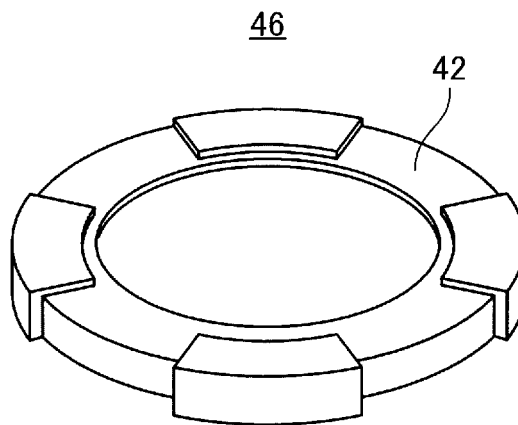
[図12]



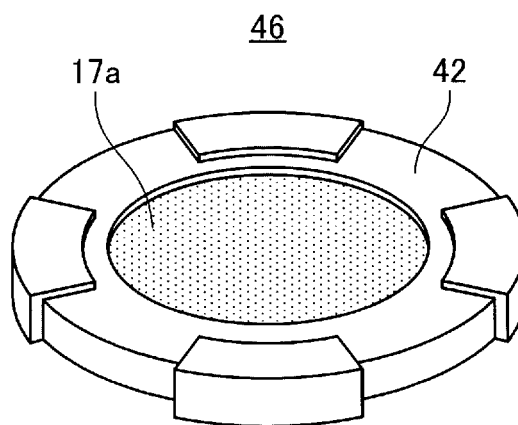
[図13A]



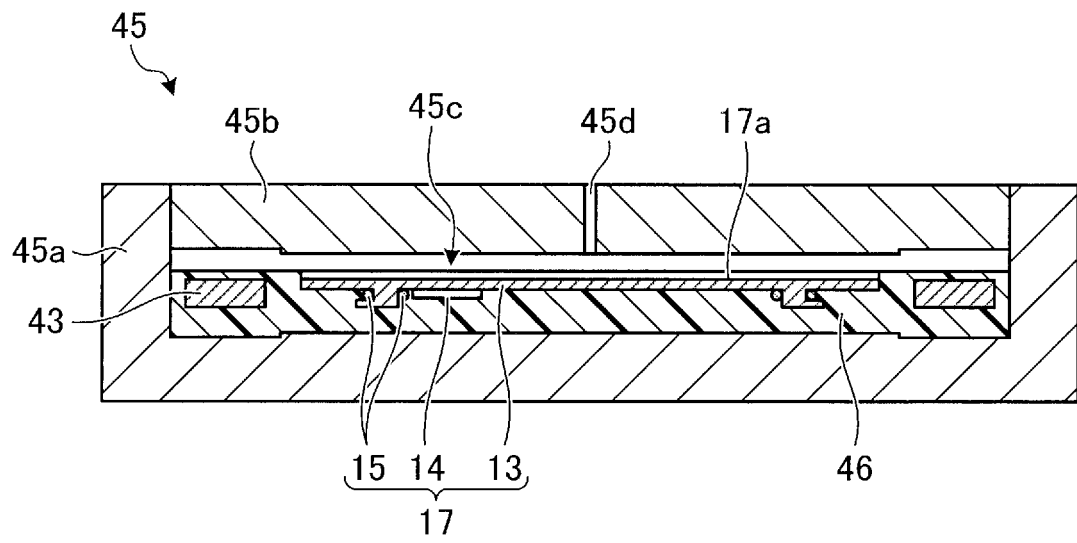
[図13B]



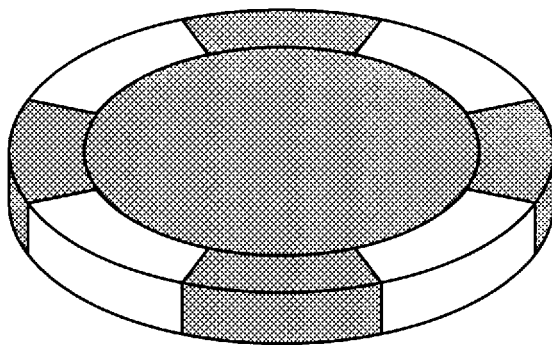
[図13C]



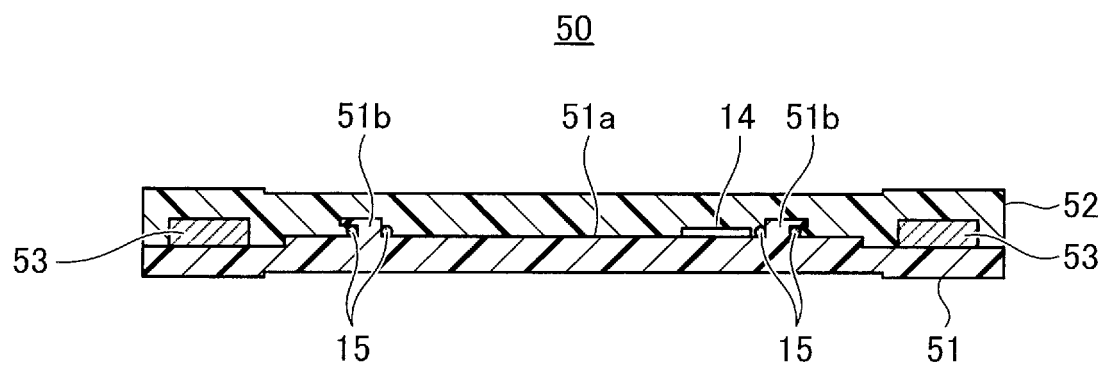
[図13D]



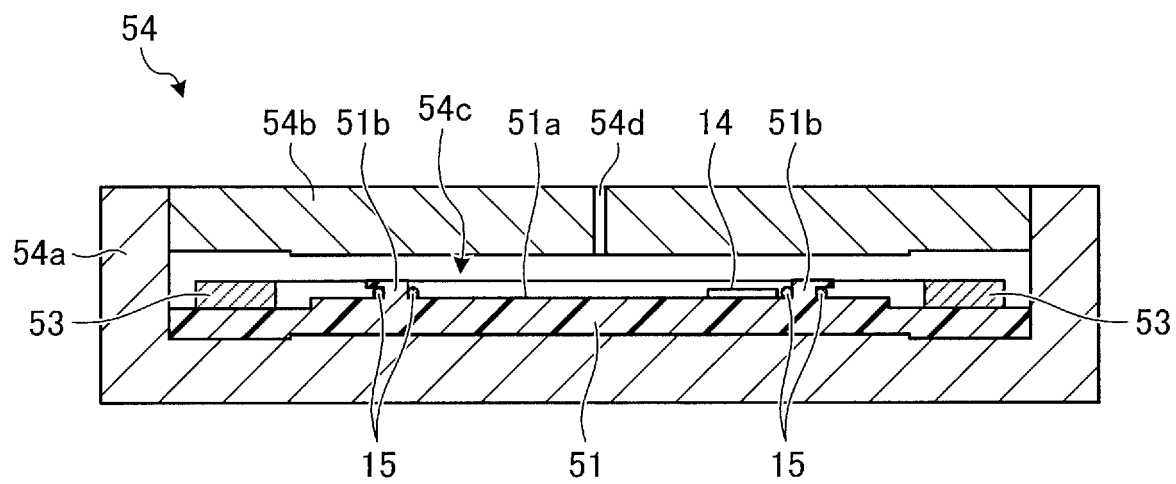
[図13E]

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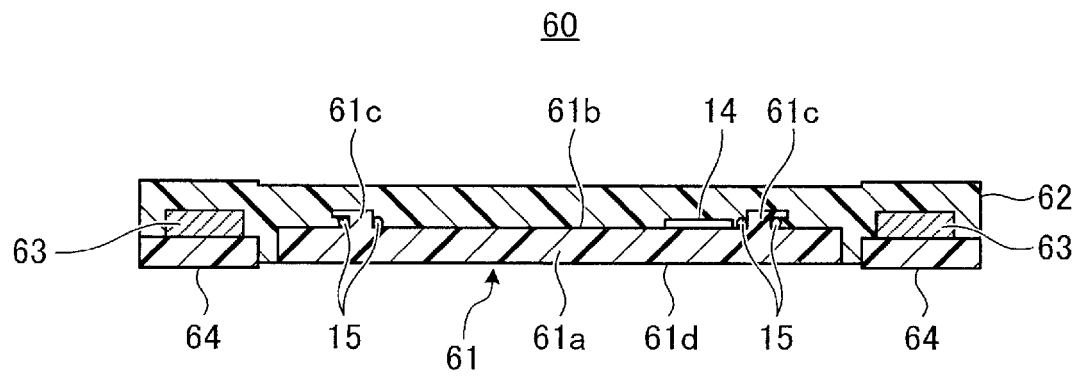
[図14]



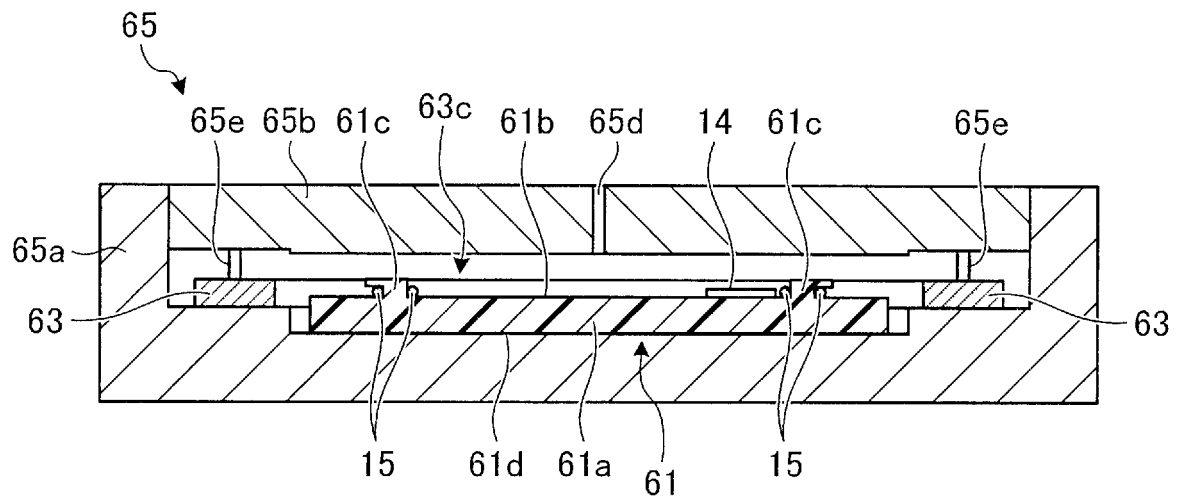
[図15]



[図16]



[図17A]



[図17B]

